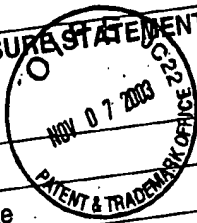


U.S. Department of Commerce, Patent and Trademark Office (PTO Form 1449 modified)		Docket No. AMAT/6392/DSM/LO W K/JW	Serial No. 10/010,950
SUPPLEMENTAL INFORMATION DISCLOSURE STATEMENT BY APPLICANT		Applicant Xia, et al.	Confirmation No.: 5694
(Use several sheets if necessary)		Filing Date November 13, 2001	Group 2818



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*Examiner Initial		Document Number	Issue Date	Applicant(s) Name	Class	Subclass	Filing Date if Appropriate
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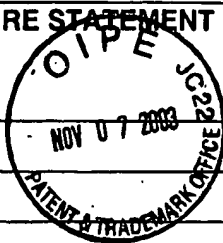
*Examiner Initial		Document Number	Date	Country	Class	Subclass	Translation	
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<i>De</i>	B1	09-008031	01/10/1997	JP	H01L	21/316	<input type="checkbox"/>	<input checked="" type="checkbox"/>
	B2	00/19498	04/06/2000	WO	H01L	21/027	<input type="checkbox"/>	<input checked="" type="checkbox"/>
	B3	1 176 226	01/30/2002	EP	C23C	16/32	<input type="checkbox"/>	<input checked="" type="checkbox"/>

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*Examiner Initial		Including Author, Title, Date, Pertinent Pages, Etc.
<i>De</i>	C1	U.S. Patent Application No. 09/270,039, filed on March 16, 1999.
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\*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with your communication to applicant.

U.S. Department of Commerce, Patent and Trademark Office (PTO Form 1449 modified)		Docket No. AMAT/6392/DSM/LO W K/JW	Serial No. 10/010,950
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(Use several sheets if necessary)		Filing Date November 13, 2001	Group 2818
Examiner     Dung Anh Le			



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	C8	PCT International Search Report for US/02/40034, dated May 19, 2003.
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Examiner		Date Considered Feb-04

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